

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Yee-Chia Yeo, et al.

Docket No.:

TS01-1132C (24061.398)

Serial No.:

10/730,778

Examiner:

Richard A. Booth

Filing Date:

December 9, 2003

Art Unit:

2812

For:

Complementary Metal Oxide

99999999

Conf. No.:

4830

Semiconductor Transistor Technology Using Selective Epitaxy of a Strained Silicon

Layer Germanium

RESPONSE TO RESTRICTION REQUIREMENT

Mail Stop: Amendment Commissioner for Patents PO Box 1450

Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed April 22, 2005, applicant hereby elects Group II, Claims 28-32, which is drawn to a CMOS device..

Applicant's election is made with traverse on the grounds that the embodiments delineated by the examiner are not patentably distinct and therefore constitute a single invention concept.

An early action on the merits is respectfully requested.

Respectfully submitted,

David M. O'Dell

Reg. No. 42,044

Date: 5-9-05

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Mail Stop: Amendment, Commissioner For Patents, PO Box 1450, Alexandria, VA 22313-1450 on the date below.

Name

Date